# UNISONIC TECHNOLOGIES CO., LTD

UT2302 **Power MOSFET** 

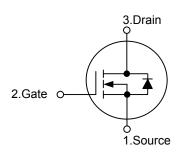
# **N-CHANNEL ENHANCEMENT MODE**

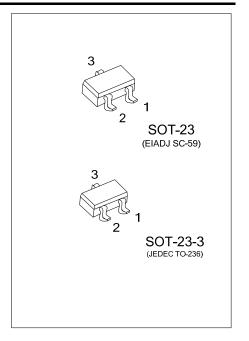
#### **DESCRIPTION**

The UTC UT2302 is N-channel Power MOSFET, designed with high density cell, with fast switching speed, ultra low on-resistance, and excellent thermal and electrical capabilities.

Used in commercial and industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

#### **SYMBOL**

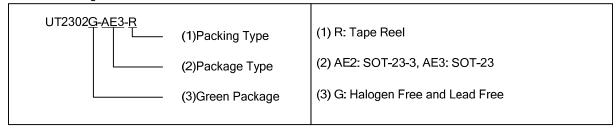




#### **ORDERING INFORMATION**

Ordering Number	Package	Pin Assignment			Deakins	
		1	2	3	Packing	
UT2302G-AE2-R	SOT-23-3	S	G	D	Tape Reel	
UT2302G-AE3-R	SOT-23	S	G	D	Tape Reel	

Pin Assignment: G: Gate D: Drain S: Source Note:



#### **MARKING**



UT2302

#### ■ **ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{ extsf{DSS}}$	20	V
Gate-Source Voltage		$V_{GSS}$	±8	V
Drain Current (Note 1)	Continuous	I <sub>D</sub>	2.4	Α
	Pulsed	I <sub>DM</sub>	10	Α
Power Dissipation		$P_D$	1.25	W
Junction Temperature		$T_J$	+150	°C
Storage Temperature		T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### **■ THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note 3)	$\theta_{JA}$	100	°C/W

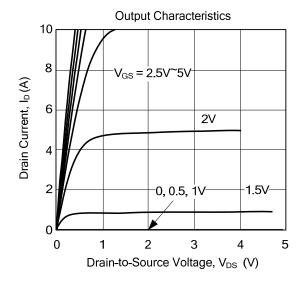
## ■ ELECTRICAL CHARACTERISTICS (Ta =25°C, unless otherwise specified)

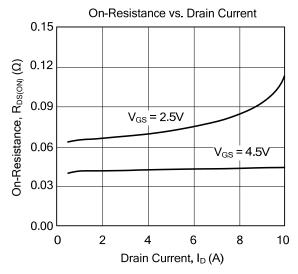
PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0 V, I <sub>D</sub> =250 μA				V		
Drain-Source Leakage Current	$I_{DSS}$	V <sub>DS</sub> =20 V, V <sub>GS</sub> =0 V			1.0	μΑ		
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}$ =0 V, $V_{GS}$ = ±8V			±100	nA		
ON CHARACTERISTICS								
Gate-Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	0.45			V		
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5 V, I <sub>D</sub> =7.2 A			50	mΩ		
		V <sub>GS</sub> =2.5 V, I <sub>D</sub> =3.1 A		75	95	mΩ		
On State Drain Current (Note2)	$I_{D(ON)}$	$V_{DS} \ge 5V$ , $V_{GS} = 4.5 V$	6			Α		
DYNAMIC PARAMETERS								
Input Capacitance	$C_{ISS}$			450		pF		
Output Capacitance	Coss	V <sub>DS</sub> =10 V, V <sub>GS</sub> =0V, f=1MHz		70		pF		
Reverse Transfer Capacitance	$C_{RSS}$			43		pF		
SWITCHING PARAMETERS								
Turn-ON Delay Time	$t_{D(ON)}$			7	15	ns		
Turn-ON Rise Time	$t_{R}$	$V_{DD}$ =10V, $R_L$ =10 $\Omega$ , $I_D$ =1A,		55	80	ns		
Turn-OFF Delay Time	$t_{D(OFF)}$	$V_{GEN}$ =4.5V, $R_G$ =6 $\Omega$		16	60	ns		
Turn-OFF Fall-Time	$t_{F}$			10	25	ns		
Total Gate Charge	$Q_G$			5.2	10	nC		
Gate-Source Charge	$Q_GS$	$V_{DS}$ =10V, $V_{GS}$ =4.5 V, $I_{D}$ =3.6 A		0.65		nC		
Gate-Drain Charge	$Q_GD$			1.5		nC		
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS								
Drain-Source Diode Forward Voltage	$V_{SD}$	V <sub>GS</sub> =0 V, I <sub>S</sub> =1.0 A		0.76	1.2	V		
Maximum Continuous Drain-Source Diode Forward Current	Is				1.6	Α		

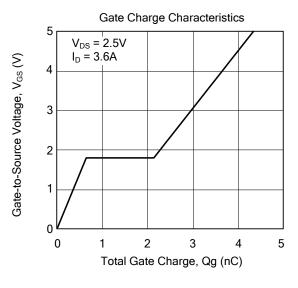
Notes: 1. Repetitive Rating: Pulse width limited by T<sub>J</sub>

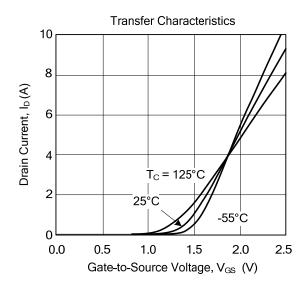
- 2. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%
- 3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board

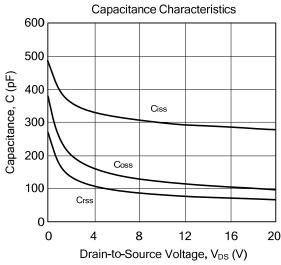
#### ■ TYPICAL CHARACTERISTICS

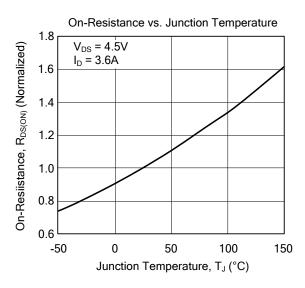




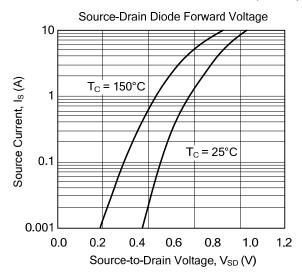


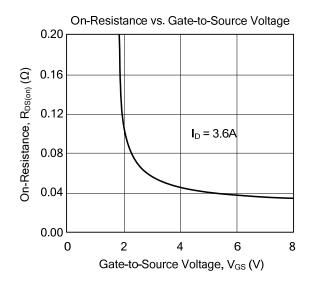


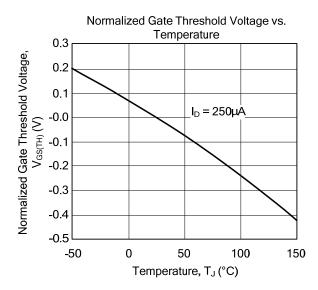


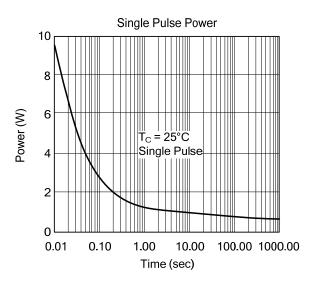


## TYPICAL CHARACTERISTICS(Cont.)

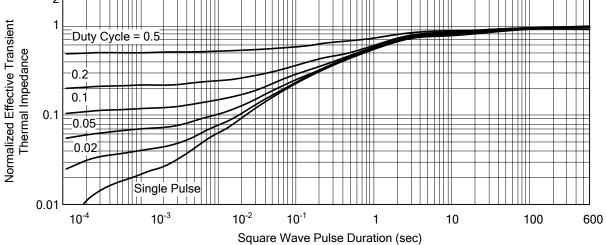












Normalized Thermal Transient Impedance, Junction-to-Ambient

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Unisonic manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60\_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3